

Smart High-Side Power Switch

One Channel: $60m\Omega$

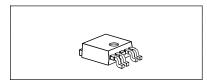
Status Feedback

Product Summary

On-state Resistance	R _{on}	60mΩ
Operating Voltage	$V_{bb(on)}$	4.7541V
Nominal load current	$I_{L(NOM)}$	7.0A
Current limitation	$I_{L(SCr)}$	17A

- · AEC qualified
- Green product (RoHS compliant)

Package



PG-TO-252

General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.
- Providing embedded protective functions

Applications

- µC compatible high-side power switch with diagnostic feedback for 5V, 12V and 24V grounded loads
- All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- · Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Improved electromagnetic compatibility (EMC)
- Fast demagnetization of inductive loads
- Stable behaviour at undervoltage
- Wide operating voltage range
- Logic ground independent from load ground

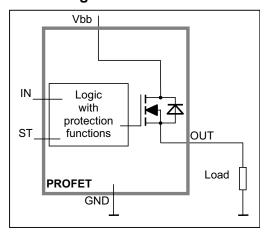
Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge protection (ESD)

Diagnostic Function

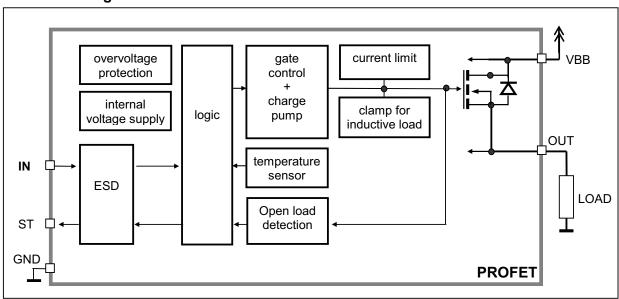
- Diagnostic feedback with open drain output
- Open load detection in ON-state
- Feedback of thermal shutdown in ON-state

Block Diagram



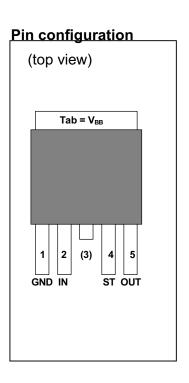


Functional diagram



Pin Definitions and Functions

Pin	Symbol	Function	
1	GND	Logic ground	
2	IN	Input, activates the power switch in case of logical high signal	
3	V _{bb}	Positive power supply voltage The tab is shorted to pin 3	
4	ST	Diagnostic feedback, low on failure	
5	OUT	Output to the load	
Tab	V _{bb}	Positive power supply voltage The tab is shorted to pin 3	





Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{ m bb}$	43	V
Supply voltage for full short circuit protection $T_{\rm jStart}$ =-40+150°C	$V_{ m bb}$	24	V
Load dump protection ¹) $V_{\text{LoadDump}} = V_{\text{A}} + V_{\text{S}}$, $V_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{2} = 2 \Omega$, $R_{\text{L}} = 4.0 \Omega$, $t_{\text{d}} = 200 \text{ ms}$, IN= low or high	V _{Load dump} ³)	60	V
Load current (Current limit, see page 5)	<i>I</i> L	self-limited	Α
Operating temperature range	$T_{\rm j}$	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC), T _C ≤ 25 °C	P _{tot}	75	W
Maximal switchable inductance, single pulse V_{bb} = 12V, $T_{j,start}$ = 150°C, T_{C} = 150°C const. (See diagram on page 9) $I_{L(ISO)}$ = 7 A, R_{L} = 0 Ω ; $E^{4)}_{AS}$ =0.19J:	Zı	5.6	mH
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF	V _{ESD}	1.0 4.0 8.0	kV
Input voltage (DC)	V _{IN}	-10 +16	V
Current through input pin (DC)	I _{IN}	±2.0	mA
Current through status pin (DC)	I _{ST}	±5.0	
see internal circuit diagrams page 8			

Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case:	R_{thJC}			1.67	K/W
	junction - ambient (free air):	R _{thJA}			75	
	device on pcb ⁵):			42		

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 $^{^{1)}}$ Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended).

 $R_{\rm l}$ = internal resistance of the load dump test pulse generator

V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

 E_{AS} is the maximum inductive switch-off energy Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μ m thick) copper area for V_{bb} connection. PCB is vertical without blown air.

Values

30

0.1

0.1

100

200

V/µs

V/µs

Unit



Electrical Characteristics

Parameter and Conditions

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at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	
Load Switching Capabilities and Characteristic	s				
On-state resistance (pin 3 to 5)					
$I_L = 2 \text{ A}; V_{BB} \ge 7V$ $T_j = 25 \text{ °C}$	R_{ON}		50	60	mΩ
$I_{L} = 2 \text{ A}; V_{BB} \ge 7V$ $T_{j} = 25 \text{ °C}$ $T_{i} = 150 \text{ °C}$:		100	120	
see diagram, page 10					
Nominal load current, (pin 3 to 5)					
ISO 10483-1, 6.7:V _{ON} =0.5V, T _C =85°C	I _{L(ISO)}	5.8	7.0		A
Output current (pin 5) while GND disconnected or	I _{L(GNDhigh)}			2	mA
GND pulled up ⁶), V_{bb} =30 V, V_{IN} = 0, see diagram page 8					
Turn-on time IN to 90% V _{OUT} .	: <i>t</i> _{on}	30	100	200	μs

IN \square to 10% V_{OUT} :

 $t_{\rm off}$

 dV/dt_{on}

 $-dV/dt_{off}$

Symbol

Operating Parameters

10 to 30% V_{OUT} , $R_L = 12 \Omega$,

70 to 40% V_{OUT} , $R_L = 12 \Omega$,

Turn-off time

 $R_{\rm L}$ = 12 Ω , Slew rate on

Slew rate off

o por a an a moror o						
Operating voltage	<i>T</i> _j =-40 <i>T</i> _j =+25+150°C:	V _{bb(on)}	4.75		41 43	V
Overvoltage protection ⁷⁾ I _{bb} =40 mA	$T_{\rm j}$ =-40°C: $T_{\rm j}$ =25+150°C:	$V_{\rm bb(AZ)}$	41 43	 47	 52	V
Standby current (pin 3) 8) V _{IN} =0; see diagram on page 10	T _j =-40+25°C: T _j = 150°C:	I _{bb(off)}		5 	9 25	μΑ
Off-State output current (included in I _{bb(off)}) Vin=0		I _{L(off)}		1	10	μА
Operating current ⁹⁾ , V _{IN} =5 V		I _{GND}		0.8	1.5	mA

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not subject to production test, specified by design

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150 Ω resistor for the GND connection is recommended. See also $V_{\rm ON(CL)}$ in table of protection functions and circuit diagram page 8.

Measured with load

Add I_{ST} , if $I_{ST} > 0$, add I_{IN} , if $V_{IN} > 5.5 \text{ V}$



(on-condition)

Smart High-Side Power Switch BTS428L2

Parameter and Conditions	Symbol		Values		Unit
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	
Protection Functions ¹⁰)					
Current limit (pin 3 to 5)	I _{L(lim)}				
(see timing diagrams on page 12) $ T_{j} = -40^{\circ}\text{C:} $ $ T_{j} = 25^{\circ}\text{C:} $ $ T_{j} = +150^{\circ}\text{C:} $		21 17 12	28 22 16	36 31 24	A
Repetitive short circuit shutdown current limit	I _{L(SCr)}				
$T_j = T_{jt}$ (see timing diagrams, page 12)			17		Α
Thermal shutdown time ¹¹ $T_{j,start} = 25^{\circ}C$:	t _{off(SC)}		7.5		ms
(see timing diagrams on page 12)					
Output clamp (inductive load switch off) at $V_{OUT} = V_{bb} - V_{ON(CL)}$ $I_{L} = 40 \text{ mA}$:	V _{ON(CL)}	41 43	47	52	V
Thermal overload trip temperature	$T_{\rm jt}$	150			°C
Thermal hysteresis	$\Delta T_{\rm jt}$		10		K
Reverse battery (pin 3 to 1) 12)	-V _{bb}			32	V
Reverse battery voltage drop $(V_{out} > V_{bb})^{13}$) $I_L = -2 \text{ A}$ $T_j = 150 \text{ °C}$:	-V _{ON(rev)}		600		mV
Diagnostic Characteristics					
Open load detection current	I _{L (OL)}	10		500	mA

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Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 8).

¹³⁾ not subject to production test, specified by design



Smart High-Side Power Switch BTS428L2

Parameter and Conditions	arameter and Conditions Symbol Values		;	Unit	
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise spec	fied	min	typ	max	
Input and Status Feedback ¹⁴)					
Input resistance see circuit page 8	Rı	2.5	3.5	6	kΩ
Input turn-on threshold voltage	$V_{IN(T^+)}$	1.7		3.2	V
Input turn-off threshold voltage	$V_{IN(T-)}$	1.5			V
Input threshold hysteresis	$\Delta V_{\text{IN(T)}}$		0.5		V
Off state input current (pin 2), $V_{IN} = 0.4 \text{ V}$	I _{IN(off)}	1		50	μΑ
On state input current (pin 2), V _{IN} = 5 V	I _{IN(on)}	20	50	90	μА
Delay time for status with open load after switch (see timing diagrams on page 12)	h off $t_{d(ST\;OL4)}$	100	520	900	μs
Status output (open drain)					
Zener limit voltage $I_{ST} = +1$.	6 mA: $V_{ST(high)}$	5.4	6.1	. 	V
ST low voltage $I_{ST} = +1$.	6 mA: $V_{ST(low)}$			0.4	

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 $[\]overline{\ }^{14)}$ If a ground resistor R_{GND} is used, add the voltage drop across this resistor.



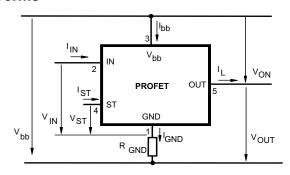
Truth Table

	Input	Output	Status
	level	level	BTS 428L2
Normal	L	L	Н
operation	Н	Н	Н
Open load	L	Z	Н
-	Н	Н	L
Overtem-	L	L	Н
perature	Н	L	L

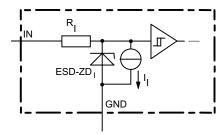
L = "Low" Level H = "High" Level X = don't care Z = high impedance, potential depends on external circuit Status signal after the time delay shown in the diagrams (see fig 5. page 12)



Terms

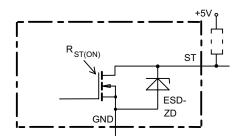


Input circuit (ESD protection)



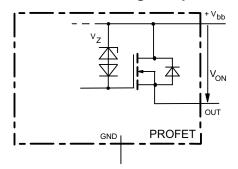
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

Status output

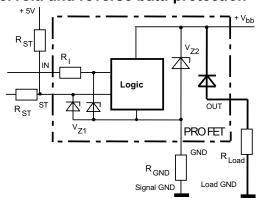


ESD-Zener diode: 6.1 V typ., max 5.0 mA; RsT(ON) < 375 Ω at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp



Overvolt. and reverse batt. protection

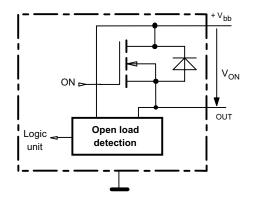


 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_{I} = 3.5 kΩ typ.

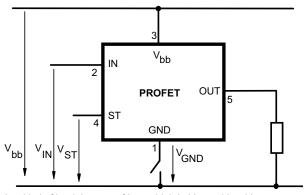
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

Open-load detection in on-state

Open load, if $V_{ON} < R_{ON} \cdot I_{L(OL)}$; IN high



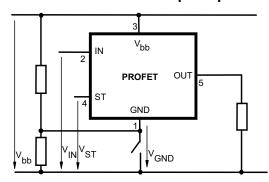
GND disconnect



Any kind of load. In case of Input=high is $V_{OUT} \approx V_{IN}$ - $V_{IN(T+)}$. Due to V_{GND} >0, no V_{ST} = low signal available.

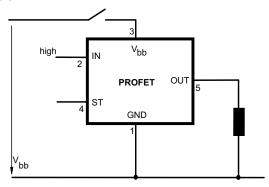


GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN}$ - $V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no V_{ST} = low signal available.

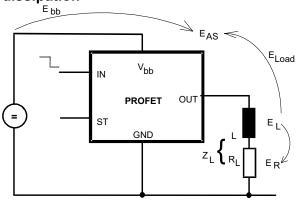
V_{bb} disconnect with energized inductive load



For inductive load currents up to the limits defined by $\rm Z_L$ (max. ratings and diagram on page 9) each switch is protected against loss of $\rm V_{bb}$.

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive Load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = \frac{1}{2} \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

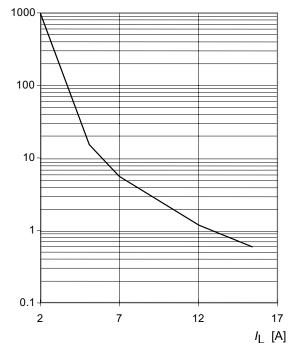
with an approximate solution for $R_L > 0 \Omega$:

$$E_{\text{AS}} = \frac{I_{\text{L}} \cdot L}{2 \cdot R_{\text{L}}} \cdot \left(V_{\text{bb}} + |V_{\text{OUT(CL)}}| \right) \cdot \ln \left(1 + \frac{I_{\text{L}} \cdot R_{\text{L}}}{|V_{\text{OUT(CL)}}|} \right)$$

Maximum allowable load inductance for a single switch off

$$L = f(I_L); T_{j,start} = 150$$
°C, $T_C = 150$ °C const.,
 $V_{bb} = 12 \text{ V}, R_L = 0 \Omega$

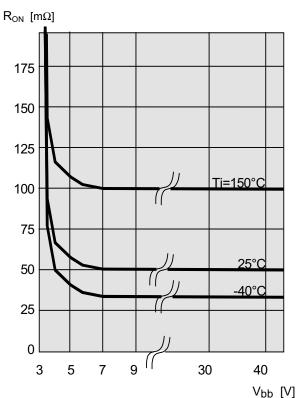
 Z_L [mH]





Typ. on-state resistance

$$R_{ON} = f(V_{bb}, T_j); I_L = 2 A, IN = high$$



Typ. standby current

 $I_{bb(off)} = f(T_j)$; $V_{bb} = 9...34 \text{ V}$, IN1,2 = low

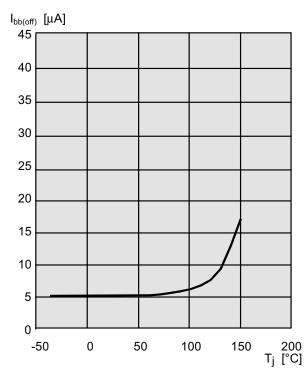
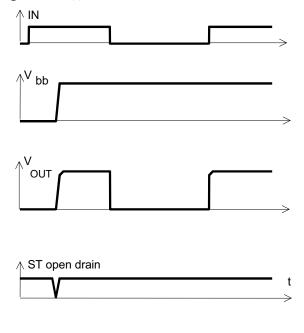




Figure 1a: V_{bb} turn on:



proper turn on under all conditions

Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:

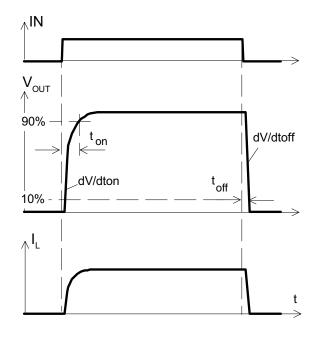
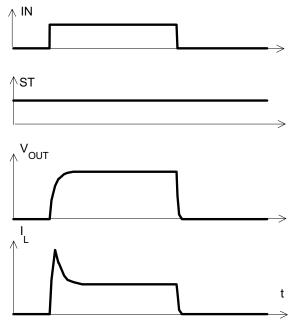
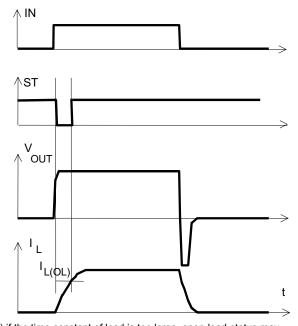


Figure 2b: Switching a lamp,



The initial peak current should be limited by the lamp and not by th current limit of the device.

Figure 2c: Switching an inductive load

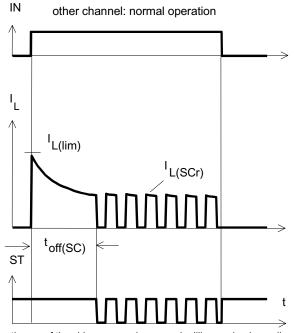


 $\ensuremath{^*}\xspace$) if the time constant of load is too large, open-load-status may occur

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Figure 3a: Short circuit shut down by overtemperature, reset by cooling



Heating up of the chip may require several milliseconds, depending on external conditions

Figure 4a: Overtemperature: Reset if $T_i < T_{it}$

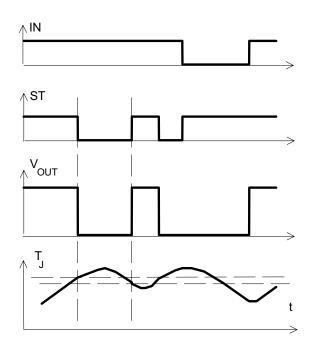


Figure 5a: Open load: detection in ON-state, open load occurs in on-state

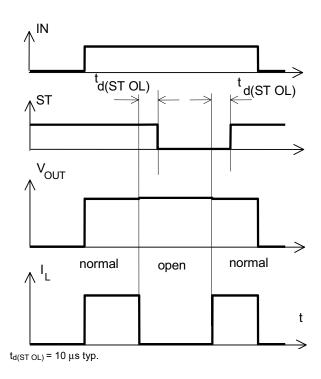
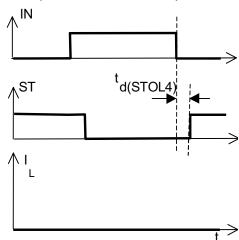


Figure 5b: Open load: turn on/off to open load





Package Outlines

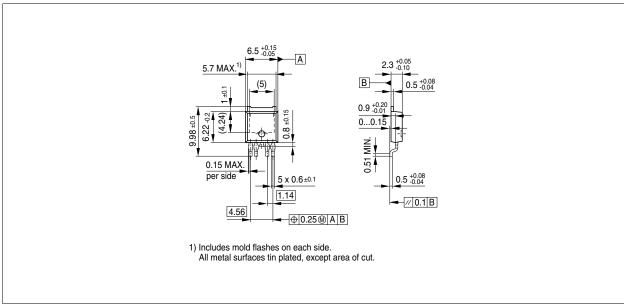


Figure 1 PG-TO-252 (Plastic Dual Small Outline Package) (RoHS-compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pbfree finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Please specify the package needed (e.g. green package) when placing an order

Dimensions in mm



Revision History

Version	Date	Changes
V1.1	2007-05-29	Creation of the green datasheet.
		First page :
		Adding the green logo and the AEC qualified
		Adding the bullet AEC qualified and the RoHS compliant features
		Package page
		Modification of the package to be green.

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